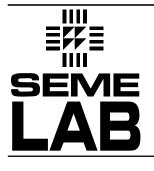
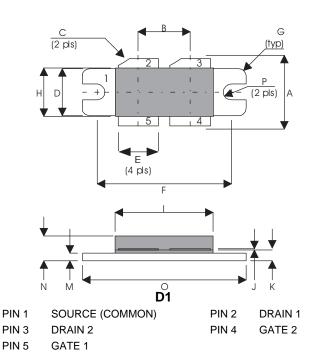
TetraFET

DMD1028 DMD1028-A



ROHS COMPLIANT METAL GATE RF SILICON FET

MECHANICAL DATA



DIM	Millimetres	Tol.	Inches	Tol.
Α	15.24	0.50	0.600	0.020
В	10.80	0.13	0.425	0.005
С	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	8.38	0.13	0.330	0.005
F	27.94	0.13	1.100	0.005
G	1.52R	0.13	0.060R	0.005
Н	10.16	0.15	0.400	0.006
I	21.84	0.23	0.860	0.009
J	0.10	0.02	0.004	0.001
Κ	1.96	0.13	0.077	0.005
М	1.02	0.13	0.040	0.005
Ν	4.45	0.38	0.175	0.015
0	34.04	0.13	1.340	0.005
Р	1.63R	0.13	0.064R	0.005

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 300W – 28V – 175MHz PUSH–PULL

FEATURES

- SUITABLE FOR BROAD BAND APPLICATIONS
- SIMPLE BIAS CIRCUITS
- ULTRA-LOW THERMAL RESISTANCE
- BeO FREE
- LOW Crss
- HIGH GAIN 16 dB MINIMUM

APPLICATIONS

• VHF/UHF COMMUNICATIONS from 1 MHz to 400 MHz

P _D	Power Dissipation	875W (438W -A Version)
BV _{DSS}	Drain – Source Breakdown Voltage *	70V
BV _{GSS}	Gate – Source Breakdown Voltage*	±20V
I _{D(sat)}	Drain Current*	30A
T _{stg}	Storage Temperature	–65 to 150°C
Тj	Maximum Operating Junction Temperature	200°C

* Per Side



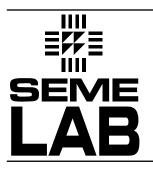
ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
	PER SIDE						
BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0	I _D = 100mA	70			V
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 28V	V _{GS} = 0			6	mA
I _{GSS}	Gate Leakage Current	V _{GS} = 20V	$V_{DS} = 0$			1	μA
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 _{fs}	Forward Transconductance*	V _{DS} = 10V	I _D = 6A	4.8			mhos
V _{GS(th)m}	Gate Threshold Voltage atch Matching Between Sides	I _D = 10mA	V _{DS} = V _{GS}			0.1	V
	TOTAL DEVICE						
G _{PS}	Common Source Power Gain	P _O = 300W		16			dB
η	Drain Efficiency	V _{DS} = 28V	I _{DQ} = 2A	60			%
VSWR	Load Mismatch Tolerance	f = 175MHz		20:1			—
PER SIDE							
C _{iss}	Input Capacitance	$V_{DS} = 28V$	$V_{GS} = -5V f = 1MHz$			360	pF
C _{oss}	Output Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ f = 1MHz			180	pF
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ f = 1MHz			15	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 0.2°C / W
,		0.4 °C / W -A Version



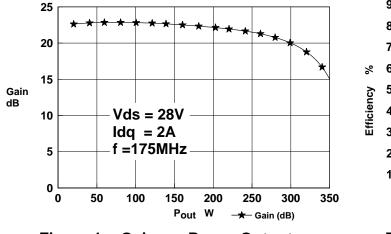
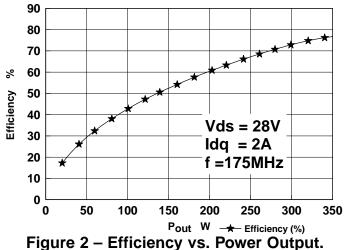


Figure 1 – Gain vs. Power Output.



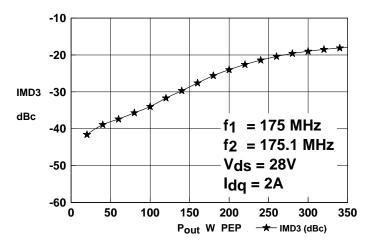


Figure 3 – IMD vs. Power Output



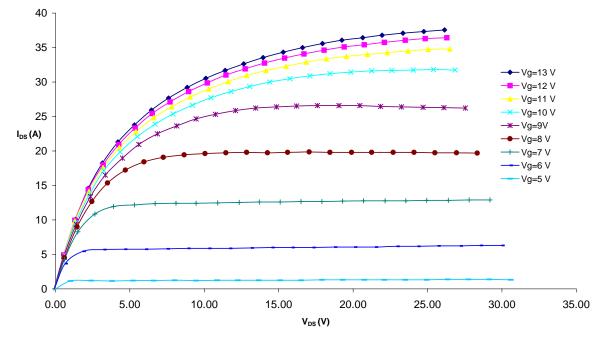
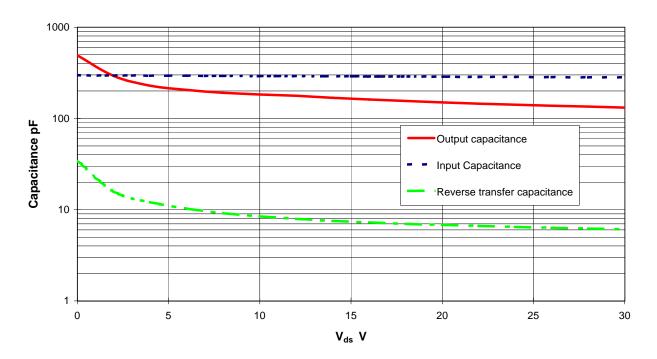
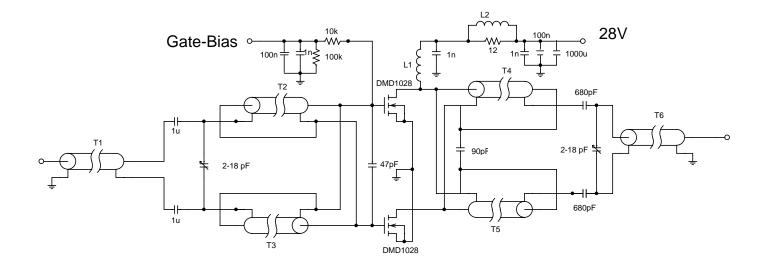


Figure 4 – Typical IV Characteristics.









DMD1028 175MHz TEST FIXTURE

Substrate 1.6mm PTFE/glass, Er=2.5 All microstrip lines W=4.4mm

- T1,2,3 7cm Storm Products EXE18 19/30 S1TW coaxial cable on Siemens B62152A1X1 2-hole core.
- T4,5 14cm Storm Products EXE18 19/30 S1TW coaxial cable.
- T6 11cm Storm Products EXE18 19/30 S1TW coaxial cable
- L1 6 turns 1.2mm dia wire, 5mm internal diameter
- L2 1.5 turns 0.9mm dia wire on Siemens A1 x 1 2 hole core

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